

Cont A3
is provided with a means for impressing direct current or
alternating current power.

Please add the following:

A4
8. The semiconductor manufacturing apparatus according to
Claim 2, wherein said vacuum vessel can be divided into a part
including said processing chamber and a part having said
substrate transport mechanism.

9. The semiconductor manufacturing apparatus according to
Claim 2 comprising a plasma generation mechanism for generating
plasma in said processing chamber.

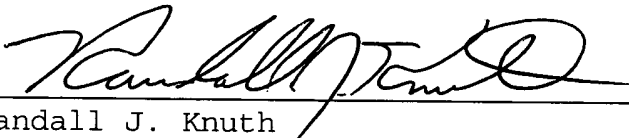
10. The semiconductor manufacturing apparatus according to
Claim 3 comprising a plasma generation mechanism for generating
plasma in said processing chamber.

11. The semiconductor manufacturing apparatus according to
Claim 10, wherein said plasma generation mechanism radiates
microwave thorough a slot antenna.

IN THE ABSTRACT

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Please delete the abstract on file and replace it with the
attached ABSTRACT OF THE DISCLOSURE.

Respectfully submitted,


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